

## WHAT IS CLAIMED IS:

1. A light emitting device comprising:
  - a thin film transistor on an insulating surface;
  - an interlayer insulating film over the thin film transistor;
  - an anode over the interlayer insulating film;
  - a wiring electrically connected to the thin film transistor and the anode;
  - a bank over the wiring and the anode;
  - a first insulating film over the anode and the bank;
  - an organic compound layer over the anode with the first insulating film interposed therebetween; and
  - a cathode over the organic compound layer.
  
2. A light emitting device comprising:
  - a thin film transistor on an insulating surface;
  - an interlayer insulating film over the thin film transistor;
  - an anode over the interlayer insulating film;
  - a wiring electrically connected to the thin film transistor and the anode;
  - a bank over the wiring and the anode;
  - a first insulating film over the anode and the bank;
  - an organic compound layer over the anode with the first insulating film interposed therebetween; and
  - a cathode over the organic compound layer,wherein the first insulating film is formed from an organic resin film.
  
3. A light emitting device comprising:
  - a thin film transistor on an insulating surface;
  - an interlayer insulating film over the thin film transistor;
  - an anode over the interlayer insulating film;
  - a wiring electrically connected to the thin film transistor and the anode;
  - a bank over the wiring and the anode;
  - a first insulating film over the anode and the bank;
  - an organic compound layer over the anode with the first insulating film interposed therebetween; and
  - a cathode over the organic compound layer,

wherein the first insulating film is at a film thickness of 1 to 5nm.

4. A light emitting device comprising:

a thin film transistor on an insulating surface;

an interlayer insulating film over the thin film transistor;

an anode over the interlayer insulating film;

a wiring electrically connected to the thin film transistor and the anode;

a bank over the wiring and the anode;

a first insulating film over the anode and the bank;

an organic compound layer over the anode with the first insulating film interposed therebetween; and

a cathode over the organic compound layer.

wherein the bank is formed from an resin insulating film.

5. A light emitting device comprising:

a thin film transistor on an insulating surface;

an interlayer insulating film over the thin film transistor;

an anode over the interlayer insulating film;

a wiring electrically connected to the thin film transistor and the anode;

a bank over the wiring and the anode;

a first insulating film over the anode and the bank;

an organic compound layer over the anode with the first insulating film interposed therebetween; and

a cathode over the organic compound layer.

wherein the anode is formed from indium thin oxide.

6. A light emitting device comprising:

a thin film transistor on an insulating surface;

an interlayer insulating film over the thin film transistor;

an anode over the interlayer insulating film;

a wiring electrically connected to the thin film transistor and the anode;

a bank over the wiring and the anode;

a first insulating film over the anode and the bank;

an organic compound layer over the anode with the first insulating film interposed therebetween; and

a cathode over the organic compound layer.

wherein the first insulating film is formed from an organic resin film;

wherein the first insulating film is at a film thickness of 1 to 5nm; and

wherein the anode is formed from indium thin oxide.

7. A device according to claim 1, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

8. A device according to claim 1, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

9. A device according to claim 1, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

10. A device according to claim 1,  
wherein the bank is processed by a plasma; and  
wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

11. A device according to claim 1,  
wherein a second insulating film is formed over the interlayer insulating film; and  
wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

12. A device according to claim 1,  
wherein the light emitting device is in combination with an electric device; and  
wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.

13. A device according to claim 2, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

14. A device according to claim 2, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

15. A device according to claim 2, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

16. A device according to claim 2,  
wherein the bank is processed by a plasma; and  
wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

17. A device according to claim 2,  
wherein a second insulating film is formed over the interlayer insulating film; and  
wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

18. A device according to claim 2,  
wherein the light emitting device is in combination with an electric device; and  
wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.

19. A device according to claim 3, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

20. A device according to claim 3, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

21. A device according to claim 3, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

22. A device according to claim 3,  
wherein the bank is processed by a plasma; and  
wherein the bank comprises a hardened film including at least an element  
selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen  
fluoride, and noble gas.

23. A device according to claim 3,  
wherein a second insulating film is formed over the interlayer insulating film; and  
wherein the second insulating film comprises at least one selected from the  
group consisting of a silicon nitride film and a diamond like carbon film.

24. A device according to claim 3,  
wherein the light emitting device is in combination with an electric device; and  
wherein the electric device is one selected from the group consisting of a  
display, a digital still camera, a notebook type personal computer, a mobile computer,  
an image reproduction apparatus including a recording medium, a goggle type display,  
a video camera and a mobile phone.

25. A device according to claim 4, wherein an average surface roughness (Ra)  
of the anode is in a range of 0.9 nm or less.

26. A device according to claim 4, wherein an average surface roughness (Ra)  
of the anode is in a range of 0.85 nm or less.

27. A device according to claim 4, wherein the interlayer insulating film  
comprises at least one selected from the group consisting of a silicon oxide film, a  
silicon nitride oxide film and a silicon oxide nitride film.

28. A device according to claim 4,  
wherein the bank is processed by a plasma; and  
wherein the bank comprises a hardened film including at least an element  
selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen  
fluoride, and noble gas.

29. A device according to claim 4,  
wherein a second insulating film is formed over the interlayer insulating film; and  
wherein the second insulating film comprises at least one selected from the  
group consisting of a silicon nitride film and a diamond like carbon film.

30. A device according to claim 4,  
wherein the light emitting device is in combination with an electric device; and  
wherein the electric device is one selected from the group consisting of a  
display, a digital still camera, a notebook type personal computer, a mobile computer,  
an image reproduction apparatus including a recording medium, a goggle type display,  
a video camera and a mobile phone.

31. A device according to claim 5, wherein an average surface roughness (Ra)  
of the anode is in a range of 0.9 nm or less.

32. A device according to claim 5, wherein an average surface roughness (Ra)  
of the anode is in a range of 0.85 nm or less.

33. A device according to claim 5, wherein the interlayer insulating film  
comprises at least one selected from the group consisting of a silicon oxide film, a  
silicon nitride oxide film and a silicon oxide nitride film.

34. A device according to claim 5,  
wherein the bank is processed by a plasma; and  
wherein the bank comprises a hardened film including at least an element  
selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen  
fluoride, and noble gas.

35. A device according to claim 5,  
wherein a second insulating film is formed over the interlayer insulating film; and  
wherein the second insulating film comprises at least one selected from the  
group consisting of a silicon nitride film and a diamond like carbon film.

36. A device according to claim 5,  
wherein the light emitting device is in combination with an electric device; and

wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.

37. A device according to claim 6, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

38. A device according to claim 6, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

39. A device according to claim 6, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

40. A device according to claim 6,  
wherein the bank is processed by a plasma; and  
wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

41. A device according to claim 6,  
wherein a second insulating film is formed over the interlayer insulating film; and  
wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

42. A device according to claim 6,  
wherein the light emitting device is in combination with an electric device; and  
wherein the electric device is one selected from the group consisting of a display, a digital still camera, a notebook type personal computer, a mobile computer, an image reproduction apparatus including a recording medium, a goggle type display, a video camera and a mobile phone.